

Substitute for Form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	Not yet assigned
				Filing Date	Herewith
				First Named Inventor:	Justin K. Brask et al.
				Art Unit	Not yet assigned
				Examiner Name	Not yet assigned
				Attorney Docket Number	042390P15744C
Sheet	1	of	2		

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)				
CX		US-	5,625,217	4/29/1997	Chau et al.	
CX		US-	5,783,478	7/21/1998	Chau et al.	
CX		US-	5,891,798	4/6/1999	Doyle et al.	
CX		US-	6,306,742 B1	10/23/2001	Doyle et al.	
CX		US-	6,184,072 B1	2/6/2001	Kaushik et al.	
CX		US-	6,420,279 B1	7/16/2002	Ono et al.	
CX		US-	6,544,906 B2	4/8/2003	Rotondaro et al.	
CX		US-	6,617,209 B1	9/9/2003	Chau et al.	
CX		US-	2003/0032303 A1	2/13/2003	Yu et al.	
CX		US-	2003/0045080 A1	3/6/2003	Visokay et al.	
		US-				
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³	Number ⁴ Kind Code ⁵ (if known)				

Examiner Signature		Date Considered	6/24/05
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Sh et	2	of	2	Attorney Docket Number	042390P15744C
NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T ²
CR		Doug Barlage et al. "High-Frequency Response of 100nm Integrated CMOS Transistors with High-K Gate Dielectrics", 2001 IEEE, 4 pgs.			
CR		Robert Chau et al., "A 50nm Depleted-Substrate CMOS Transistor (DST), 2001 IEEE, 4 pgs.			
CR		"A Method for Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/082,530, Filed February 22, 2002			
CR		"A Method for Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/285,915, Filed October 31, 2002			
CR		"A Method for Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/288,043, Filed November 5, 2002			
CR		"A Method for Making a Semiconductor Device Having an Ultra-Thin High-K Gate Dielectric", Serial No. 10/315,268, Filed December 10, 2002			
CR		"A Method for Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/338,174, Filed January 7, 2003			

Examiner Signature	<i>Christy Kovach</i>	Date Considered	6/24/05
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